

L Number	Hits	Search Text	DB	Time stamp
1	59	((silicon near (dioxide oxide)) siO siO2 siO?sub.2) same (layer coating)) and (root near mean near square near surface near roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:40
2	18	(428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (surface near roughness))) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and haze)) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (humidity rh)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:41
3	76	((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (root near mean near square near surface near roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:41
4	12	((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((relative near humifity) rh!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:41
5	33	((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((humidity) rh!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:41
6	72	428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) same haze)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:42
7	99	((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2)) and (root near mean near square near surface near roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:42
8	25	(((((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing))) and (alkylchlorosilane dimethyldichlorosilane trimethylchlorosilane CH32Cl2Si CH32SiCl2 CH3cl3Si ch3sicl3 (ch?sub.3 near ?sub.2 near cl?sub.2 near Si) (ch?sub.3 near ?sub.2 near si near cl?sub.2) (ch?sub.3 near cl?sub.3 near si) (ch?sub.3 near si near cl?sub.3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:43
9	129	((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:43
10	59	((silicon near (dioxide oxide)) siO siO2 siO?sub.2) same (layer coating)) and (root near mean near square near surface near roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:43
11	76	((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (root near mean near square near surface near roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:44
12	18	(428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (surface near roughness))) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and haze)) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 siO?sub.2) same (layer coating)) and (humidity rh)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:44
13	12	((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((relative near humifity) rh!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:44
14	33	((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((humidity) rh!)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:44

15	72	428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO2 sio?sub.2) same (layer coating)) same haze)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:44
16	99	(((silicon near (dioxide oxide)) silica siO siO2 sio?sub.2)) and (root near mean near square near surface near roughness)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:44
17	25	((((silicon near (dioxide oxide)) silica siO siO2 sio?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing))) and (alkylchlorosilane dimethyldichlorosilane trimethylchlorosilane CH32Cl2Si CH32SiCl2 CH3cl3Si ch3sicl3 (ch?sub.3 near ?sub.2 near cl?sub.2 near Si) (ch?sub.3 near ?sub.2 near si near cl?sub.2) (ch?sub.3 near cl?sub.3 near si) (ch?sub.3 near si near cl?sub.3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:45
18	129	((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) and (((silicon near (dioxide oxide)) silica siO siO2 sio?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:45

19	34	<p> ((((silicon near (dioxide oxide)) siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (root near mean near square near surface near roughness) ) ((428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (surface near roughness))) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and haze)) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (humidity rh))) ) (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (root near mean near square near surface near roughness) ) (((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((relative near humifity) rh!) ) (((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((humidity) rh!) ) (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) same haze) ) (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2)) and (root near mean near square near surface near roughness) ) (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing))) and (alkylchlorosilane dimethyldichlorosilane trimethylchlorosilane CH<sub>3</sub>2Cl<sub>2</sub>Si CH<sub>3</sub>2SiCl<sub>2</sub> CH<sub>3</sub>cl<sub>3</sub>Si ch<sub>3</sub>sicl<sub>3</sub> (ch?sub.3 near ?sub.2 near cl?sub.2 near Si) (ch?sub.3 near ?sub.2 near si near cl?sub.2) (ch?sub.3 near cl?sub.3 near si) (ch?sub.3 near si near cl?sub.3) ) (((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing))) ) (((silicon near (dioxide oxide)) siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (root near mean near square near surface near roughness) ) (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (root near mean near square near surface near roughness) ) ((428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (surface near roughness))) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and haze)) and (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (humidity rh))) ) (((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((relative near humifity) rh!) ) (((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) same ((humidity) rh!) ) (428/426,446,447.ccls. and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) same haze) ) (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2)) and (root near mean near square near surface near roughness) ) (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing))) and (alkylchlorosilane dimethyldichlorosilane trimethylchlorosilane CH<sub>3</sub>2Cl<sub>2</sub>Si CH<sub>3</sub>2SiCl<sub>2</sub> CH<sub>3</sub>cl<sub>3</sub>Si ch<sub>3</sub>sicl<sub>3</sub> (ch?sub.3 near ?sub.2 near cl?sub.2 near Si) (ch?sub.3 near ?sub.2 near si near cl?sub.2) (ch?sub.3 near cl?sub.3 near si) (ch?sub.3 near si near cl?sub.3) ) (((sicl4 sicl?sub.4 (silicon near tetrachloride)) same (vapor gas)) and (((silicon near (dioxide oxide)) silica siO siO<sub>2</sub> sio?sub.2) same (layer coating)) and (surface near roughness) ) and (vapor near (deposition deposited deposit depositing))) ) and @pd&gt;20030616 </p>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/21 15:45
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